

Practical Considerations of ASK Modulated Passive Tags

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Abstract— This paper investigates practical, wideband considerations that affect the performance of modulated passive UHF RFID tags. The tag-antenna’s structural scattering term can be favorably exploited increasing the total backscattered power, by properly selecting the circuit’s parameters within realistic values, as shown herein. Frequency domain analysis of the simplified circuit is carried out in the operational UHF frequency band. Small performance-degradation, with respect to power at the rectifier and mean backscattered power, is recorded away from resonance. However, Bit Error Rate is shown to vary greatly within the frequency band.

Keywords; RFID; ASK; passive tags; sensitivity, wideband analysis

I. INTRODUCTION

In UHF RFID communications a tag modulates a continuous wave (CW) signal transmitted by the reader, by changing its load between two states, thus changing the phase or/and the magnitude of the backscattered signal that arrives at the reader [1]. Performance of the system depends on proper load selection for the two states of the tag, so as to ensure enough backscattered power at the reader and sufficient separation in the complex plane of the backscattered fields that correspond to the two states of tag-loading.

In addition, for passive tags, where no battery source exists, their circuits are driven from the transmitted power of the reader. The ability of the tag to “wake up” and store this power represents the main limiting factor for the identification range of high frequency RFID systems [1]. As a result, it is of critical importance to draw as much of the incident power as possible. Rectification of the incident power in the tag’s circuitry has been thoroughly analyzed [1]. Another equally important parameter in the tag’s performance is the proper tag-antenna design [2]. As shown in [2], the tag’s antenna should be inductive in the operating frequency bandwidth, in order to conjugate-match the capacitance of the rectifier. A third parameter, representing the particularity of backscattering communications as opposed to classical one-way communication, is the generation of the “structural scattering term”, [3], [4], by the tag’s antenna. It has been shown (e.g. [5]) that the current on the Thévenin’s equivalent of an antenna connected to a load, does not quantify the field reradiated by the antenna (with the exception of specific antennas). Therefore, a specific term in the backscattered field has been introduced that is independent

of antenna-loading; hence the term “structural”, as it depends only on the structure of the antenna. The “structural scattering term” shapes the modulated backscattered signal, and represents a critical parameter for proper tag design. Antenna “structural mode” has been overlooked in the tag-design process until recently [6].

Extending prior-work on the field [6], [7], we elucidate the importance of the tag-antenna’s structural term in the front-end of the reader’s receiver and carry out a frequency-domain-analysis of the proposed simplified tag-design, based on realistic values from commercially available tag ICs.

II. ANTENNA BACKSCATTERING

The current at the Thévenin’s equivalent circuit of an antenna connected to a load does not quantify its backscattered field. To properly evaluate the backscattered field, we should calculate a “modified” tag’s radar cross section σ , derived in [4]:

$$\sigma = \frac{\lambda^2}{4\pi} G_{tag}^2 |\Gamma - A_s|^2 \quad (1)$$

$$\Gamma = \frac{Z_L - Z_a^*}{Z_L + Z_a}, \quad (2)$$

λ is the wavelength at the operating frequency, G_{tag} is the tag’s antenna gain and A_s is a complex parameter independent of the load that quantifies the structural mode term of the antenna. Γ expresses a modified reflection coefficient, defined in (2), where Z_L , Z_a is the load’s and the antenna’s impedance respectively.

Equation (1) is valid for a monostatic reader-antenna case and assumes no polarization mismatch. The analytical expression for a bistatic configuration with polarization mismatch can be found in [4] and does not affect the tag-design principles that will be presented in the following sections.

The term A_s can be measured or simulated for any tag’s antenna by evaluating or measuring the radar cross section for three different loads as demonstrated in [6]. Measurement examples of A_s for tag antennas can be found in [3], [8] and [9].

A_s is usually omitted in the literature for the tag. That is coming from the claim that this term doesn't influence Bit Error Rate (BER) performance of the system, since it is common in the backscattered field, regardless of the connected load. Even though this claim is correct, A_s strongly influences the total backscattered carrier power [6]; thus, the structural mode should be also taken into account.

III. ANALYSIS OF TAG'S EQUIVALENT CIRCUIT

A. Design Considerations

Let Γ_i $i=1,2$ denote the reflection coefficient for each tag's load state, given in (2) by properly setting Z_L . It was shown in [6] that proper tag design should carefully consider 2 constraints:

1) maximization of average backscattered power, expressed as:

$$\max\{\sigma_1 + \sigma_2\}, \quad (3)$$

where σ_i is given in (1), by replacing Γ with Γ_i , and 2) minimization of the BER at the reader expressed as:

$$\max\{|\Gamma_1 - \Gamma_2|\} \quad (4)$$

Constraints (3) and (4) are orthogonal. Constraint (4) is critical for the performance of the reader's detector and has been considered in the related literature (e.g. [10]). Constraint (3) is critical for the performance of the reader's front end and has been overlooked until recently [6]. The reader's antenna receives the wanted (typically small) modulated (by the tag information) backscattered signal together with strong (typically stronger) carrier reflections from the surrounding environment (e.g. due to reflections from walls or other surfaces in the vicinity of the reader). In the case of monostatic readers, an "unwanted", attenuated fraction of the strong carrier frequency also leaks into the receiver's chain through the circulator (or coupler). This problem (also common in monostatic radars) is partially controlled by implementing a "reflected power canceler" circuit like the one proposed in [11] or a carrier suppression circuit like the one in [12] (where 42dB suppression is accomplished).

The difference between these unmodulated signals and the (much smaller) backscattered modulated signal should be kept as small as possible in order to avoid desensitization of the receiver and in order for the system to operate within its spurious free dynamic range (SFDR). This parameter had been ignored, without any "disastrous" reported results. The reason for this "hidden" effect is that early RFID systems, particularly those with passive RFID tags, were forward link limited. The necessary minimum power for a passive tag to "wake up" was large, and as a consequence the average backscattered power was relatively large compared to the sensitivity of the reader's front-end. However, as the minimum threshold at the tag reduces, the reader should be able to cope with very small modulated signals (in the order of -80dBm to -90dBm), as commented in [13], [14].

By substituting (1) in (4), we find that BER minimization does not require knowledge of the structural mode term A_s . However, by substituting (1) in (3), it is found that to maximize average backscattered power, knowledge of A_s is essential.

1) Passive Tags

In the case of passive tags, maximum power transfer should be maintained at the sleeping state of the tag. Hence, an additional constraint is [7]:

$$\min\{|\Gamma_1|\} \Rightarrow \max \text{ power transfer} \quad (5)$$

B. Design Criteria

For optimal performance of passive RFID tags, we have from (5):

$$|\Gamma_1| = 0 \quad (6)$$

Then, by substituting (6) in (3) and using (2), we get:

$$\max\{|\Gamma_1 - A_s| + |\Gamma_2 - A_s|\} = \max\{|A_s| + |\Gamma_2 - A_s|\} \Rightarrow \quad (7)$$

$$|\Gamma_2| = 1, \quad \angle \Gamma_2 = \langle -A_s, \max\{|A_s|\} \rangle \quad (8)$$

Equation (8) states that the selection of load at state 2 should be such that the magnitude of the modified reflection coefficient Γ_2 should equal 1 and its phase should equal the phase of $-A_s$. Furthermore, backscattered power increases with increasing $|A_s|$. Constraint (4) is also fulfilled, because for $\Gamma_1=0$ (6), we should have $|\Gamma_2|=1$ (see (8)). The above design principles are shown in Fig. 1. We start by drawing the common term $-A_s$, represented by a vector in the complex plane. Then, we draw a circle of unit-radius centered at $-A_s$, representing the boundary of maximum $|\Gamma_i|$. The surface enclosed by that circle represents the area, where $\Gamma_1 - A_s$ and $\Gamma_2 - A_s$ could belong. After selecting the desired values for Γ_i , we can directly determine the appropriate impedance of the loads from the normalized (with respect to the antenna's resistance R_a) Smith chart, shown "faded" in Fig. 1.

An example of the effect of the structural term combined with proper selection for Γ_2 is shown in Fig. 2. We assume $|A_s|=1$, $\angle A_s=45^\circ$, $\Gamma_1=0$, $|\Gamma_2|=1$ (constraint (4) is valid), and we raise the phase of Γ_2 from 0° to 360° . Normalized backscattered power is drawn in polar plot (in dBs) with respect to its maximum value accomplished for $\angle \Gamma_2 = \angle -A_s$; an improvement of 7dBs is demonstrated, by proper selection of load at state 2.

C. Tag's Equivalent Circuit

The tag's equivalent circuit is demonstrated in Fig. 3. With respect to prior art [7], the antenna has been properly modeled, including the inductance, in order to carry out a frequency analysis of the circuit. The following design parameters are considered:

optimized for the center frequency $f_0=896.5\text{MHz}$, where we assume: $a_{f_0}=1$, $b_{f_0}=1$, d_{f_0} given by (14), and Q_{f_0} depending on the tag-chip's impedance, where the subscript f_0 denotes the value of the corresponding variable at the center frequency.

The series equivalent frequency-dependent $R_i(f)$, $X_i(f)$ values of the circuit are related to the parallel values by the following equations:

$$\begin{aligned} R_i(f) - jX_i(f) &= \frac{R_{\parallel}}{1 + (2\pi f R_{\parallel} C_{\parallel})^2} - j \frac{2\pi f R_{\parallel}^2 C_{\parallel}}{1 + (2\pi f R_{\parallel} C_{\parallel})^2} = \\ &= \frac{R_{\parallel}}{1 + k^2 Q_{f_0}^2} - j \frac{R_{\parallel} k Q_{f_0}}{1 + k^2 Q_{f_0}^2} = R_i(k) - jX_i(k) \end{aligned} \quad (15)$$

$$Q_i(f) = 2\pi f R_{\parallel} C_{\parallel} = 2\pi k f_0 R_{\parallel} C_{\parallel} = k Q_{f_0} = Q_i(k) \quad (16)$$

$$\text{and } k = f/f_0 \quad (17)$$

The real part of the tag's antenna R_a is expected to increase with frequency f , because of the resultant increase of its electrical length [2], [9]. We can approximate this variation linearly $R_a(f) = R_a(f_0) + \lambda(f - f_0)$, where λ is the appropriate slope. In [9], $\lambda=0.1$ and f_0 should be replaced in MHz. In [2], $\lambda=0.4$. Similarly the imaginary part of the antenna $X_a(f)$ is also expected to increase proportionally to $2\pi fL$ [2]. Hence the frequency variations of $a(f)$, $b(f)$ are given by:

$$\begin{aligned} a(f) &= \frac{R_i(f)}{R_a(f)} = \frac{\left[\frac{R_{\parallel}}{1 + (2\pi f R_{\parallel} C_{\parallel})^2} \right]}{R_a(f_0) + \lambda(f - f_0)} = \\ &= a_{f_0} \frac{R_{\parallel} (1 + Q_{f_0}^2)}{(1 + k^2 Q_{f_0}^2) \left[R_{\parallel} + a_{f_0} \lambda f_0 (k - 1) (1 + Q_{f_0}^2) \right]} = a(k) \end{aligned} \quad (18)$$

$$b(f) = \frac{X_a(f)}{X_i(f)} = \frac{2\pi k f_0 L}{2\pi k f_0 R_{\parallel} C_{\parallel} \sqrt{1 + (2\pi k f_0 R_{\parallel} C_{\parallel})^2}} = b(k) \quad (19)$$

For the typical values of the chip's impedance, $R_{\parallel} \sim 1.5K\Omega$, $C_{\parallel} \sim 1pF$, we have $(2\pi f R_{\parallel} C_{\parallel})^2 \gg 1$ and therefore $X_i \approx 1/(2\pi f C_{\parallel})$ (the approximated values for the three chips are given in the last column of Table I). In such case (19) is simplified to:

$$b(f) = \frac{X_a(f)}{X_i(f)} = \frac{2\pi k f_0 L}{1/2\pi k f_0 C_{\parallel}} = k^2 b_{f_0} \quad (20)$$

Similarly, for typical values of chip's impedance, we can write for the capacitance X that affects parameter d :

$$d(f) = \frac{1/2\pi f C}{1/2\pi f C_{\parallel}} = \frac{1/2\pi k f_0 C}{1/2\pi k f_0 C_{\parallel}} = d_{f_0} \quad (21)$$

Hence, d can be considered constant in the entire frequency band.

For $f_0=896.5\text{MHz}$ and the frequency varying from 865MHz to 928MHz, k increases from 0.964 to 1.035. We consider a tag with $A_s=0.6047+j0.5042$ and the "Alien Higgs" chip with $Q_{f_0}=7.18$. The antenna is power matched to the chip's impedance at f_0 . From (14) we get $d_{f_0} = -1.05$. By substituting (16), (18), (20) and (21) in (11) and (12), we calculate the vectors $\Gamma_1(f)-A_s$ and $\Gamma_2(f)-A_s$ for three values of $\lambda=\{0, 0.1, 0.4\}$. We evaluate the tag's performance in terms of three parameters: a) power at the rectifier vs the maximum power transfer at resonance f_0 in dB: $10\log_{10}[P_{rect}(f)/P_{rect}(f_0)]$ (Fig. 4), b) Backscattered power at the reader vs its value at the center frequency f_0 in dB: $10\log_{10}[P_{bsct}(f)/P_{bsct}(f_0)]$ (Fig. 5), and c) BER performance (Fig. 6) given by:

$$BER = Q\left(\sqrt{|A|/2N_0} |\Gamma_1(f) - \Gamma_2(f)|\right) \quad (22)$$

where $Q(x) = (1/\sqrt{2\pi}) \int_x^{\infty} e^{-x^2/2} dx$, A is a common term in the backscattered field in both states of the tag's load and accounts for the channel losses [10] and N_0 is the expected power of the noise level at the reader, which is considered as complex zero mean circularly symmetric Gaussian random variable.

The results of Figs. 4, 5 indicate that acceptable performance is maintained even at the margins of the frequency band. Worst case analysis shows that power at the tag decreases by 0.85dB ($\lambda=0.4$, $f=0.865\text{GHz}$), which results in approximately 9% range reduction, assuming power P decreases at an inverse square law with distance ($P \sim 1/r^2$). Backscattered power is reduced by 1.65dBs at most. However, Fig. 6 shows that BER performance of the system is very sensitive to the differences $|\Delta\Gamma(f)| = |\Gamma_1(f) - \Gamma_2(f)|$. $\Delta\Gamma$ changes from 0.71 to 1.0 within the operational frequency band. BER for these two marginal values is given in Fig. 6. It is found that for a given signal to noise ratio, the BER performance could vary greatly in the frequency band.

V. CONCLUSIONS

This work extends prior art in the field of passive RFID tag design. It is shown that the antenna structural term should be favorably exploited to increase mean backscattered power, thus improving the performance at the front-end of the reader's receiver. Furthermore, wideband analysis of the tag shows that good performance in terms of power at the rectifier and backscattered power is maintained in the entire RFID UHF frequency band. However, BER may increase significantly away from the resonant frequency.

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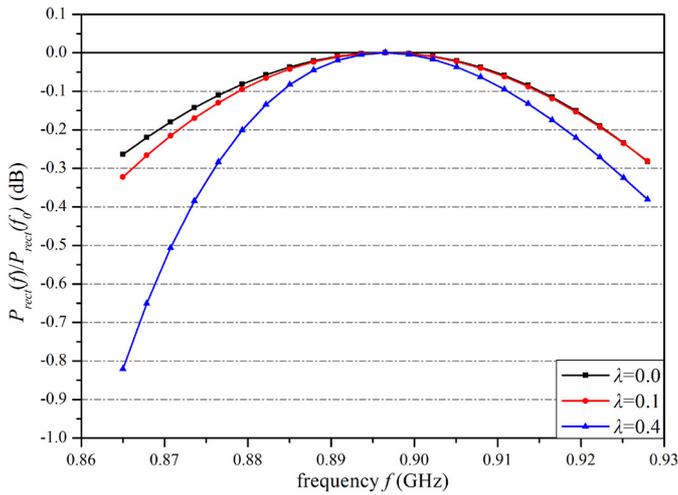


Figure 4. Power transfer to the rectifier vs. frequency.

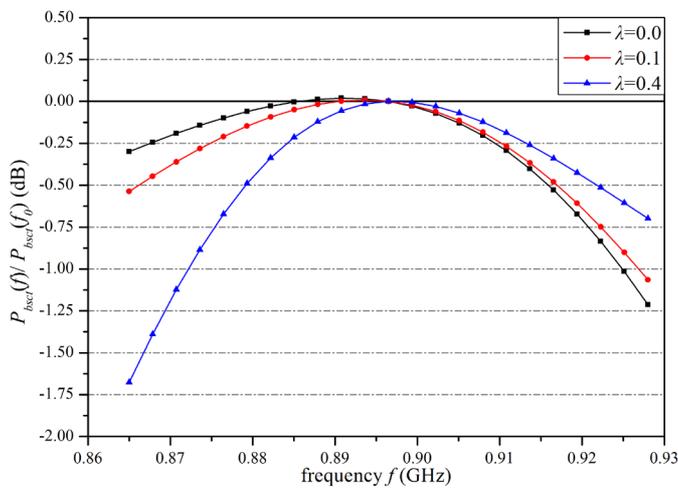


Figure 5. Backscattered power vs frequency.

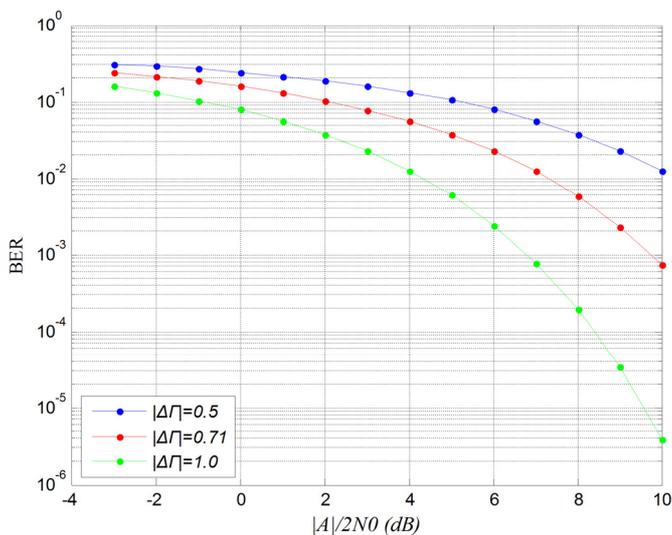


Figure 6. BER performance for the marginal cases of expected $\Delta\Gamma$.